

IN THE CLAIMS:

This listing of the claims replaces all prior versions and listings of the claims in this application.

The text of all pending claims (including any withdrawn claims) is set forth below only for the Examiner's convenience. Canceled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (Original), (Currently amended), (Canceled), (Withdrawn), (Previously presented), (New), and (Not entered).

No claims have been amended in this paper.

1. (Previously presented) A polycrystalline silicon thin film to be used in display devices, the thin film comprising primary grain boundaries, wherein adjacent ones of the primary grain boundaries are not parallel to each other, wherein an area surrounded by the primary grain boundaries is larger than $1\ \mu\text{m}^2$, wherein grains of polycrystalline silicon extend in a plurality of directions in the area from each of the primary grain boundaries, and wherein the area does not contain any substance added to promote crystallization of silicon in the area.

2. (Original) The polycrystalline silicon thin film according to claim 1, wherein the primary grain boundaries are formed in a closed curve shape or a closed polygonal shape.

3. (Original) The polycrystalline silicon thin film according to claim 1, wherein the primary grain boundaries are formed in a rectangular or a hexagonal shape.

4. (Original) The polycrystalline silicon thin film according to claim 1, wherein the primary grain boundaries are symmetrical to each other centering around a certain axis passing through the primary grain boundaries.

5. (Canceled)

6. (Original) A thin film transistor fabricated using the polycrystalline silicon thin film according to claim 1.

7. (Original) The thin film transistor according to claim 6, wherein the thin film transistor is used in an organic electroluminescent display device.

8–23. (Canceled)

24. (Previously presented) A polycrystalline silicon thin film to be used in display devices, the thin film comprising primary grain boundaries, wherein adjacent ones of the primary grain boundaries are not parallel to each other, wherein an area surrounded by the primary grain boundaries is larger than $1\text{ }\mu\text{m}^2$, and wherein polycrystalline silicon grains extend to the primary grain boundaries from an amorphous silicon portion in the area.

25. (Previously presented) The polycrystalline silicon thin film according to claim 24, wherein the primary grain boundaries are formed in a closed curve shape or a closed polygonal shape.

26. (Previously presented) The polycrystalline silicon thin film according to claim 24, wherein the primary grain boundaries are formed in a rectangular shape or a hexagonal shape.

27. (Previously presented) The polycrystalline silicon thin film according to claim 24, wherein the primary grain boundaries are symmetrical to each other centering around a certain axis passing through the primary grain boundaries.

28. (Previously presented) A thin film transistor fabricated using the polycrystalline silicon thin film according to claim 24.

29. (Previously presented) The thin film transistor according to claim 28, wherein the thin film transistor is used in an organic electroluminescent display device.

30. (Previously presented) The polycrystalline silicon thin film according to claim 1, wherein the area contains an amorphous silicon portion.

31. (Previously presented) The polycrystalline silicon thin film according to claim 30, wherein the grains of polycrystalline silicon extend from the amorphous silicon portion in the area to the primary grain boundaries surrounding the area.

32. (Previously presented) The polycrystalline silicon thin film according to claim 1, wherein each of the primary grain boundaries is a boundary where grains of polycrystalline silicon grown in different directions meet.

33. (Previously presented) The polycrystalline silicon thin film according to claim 24, wherein each of the primary grain boundaries is a boundary where polycrystalline silicon grains grown in different directions meet.